

3DD6,3DD7**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33-85, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DD6					3DD7			
			A	B	C	D	E	F	G	H	I
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300	400	500	600
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300	400	500	600
Emitter-Base Voltage	V_{EBO}	V	5					5			
Max. Collector Current	I_{CM}	A	A~F≤5.0, G~I≤3.0					A~F≤7.5, G~I≤3.5			
Max. Collector Dissipation	P_{CM}	W	50 (Tc≤75°C)					75 (Tc≤75°C)			
Junction Temperature	T_{jm}	°C	175								
Storage Temperature	T_{stg}	°C	-55~+175								
Collector-Emitter Leakage Current	I_{CEO}	mA	0.5 (A:V _{CE} =30V;B:V _{CE} =50V;C~I:V _{CE} =100V)					3.0 (A:V _{CE} =30V;B:V _{CE} =50V;C~I:V _{CE} =100V)			
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.2(A~F: I _C =2.5A, I _B =0.25A) 1.5 (G~I: I _C =1.5A, I _B =0.3A)					1.2(A~F: I _C =3.75A, I _B =0.38A) 2.0 (G~I: I _C =2.0A, I _B =0.4A)			
DC Current Gain	h_{FE}		Max.:120 Min.:15(A~F: V _{CE} =5V, I _C =2.5A) Min.: 7 (G~I:V _{CE} =10V, I _C =1.5A)					Max.:120 Min.:15 (A~F: V _{CE} =5V, I _C =3.75A) Min.: 7 (G~I:V _{CE} =10V, I _C =2.0A)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥5 (I _E =1mA)					≥5 (I _E =2mA)			

h_{FE} Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120

Outline and Dimensions: